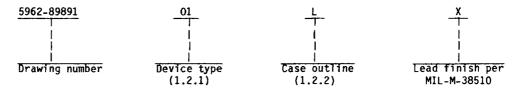
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- $1.1\,$ Scope. This drawing describes device requirements for class B microcircuits in accordance with $1.\overline{2.1}$ of MIL-STD-883, "Provisions for the use of MIL-STD-883 in conjunction with compliant non-JAN devices".
 - 1.2 Part number. The complete part number shall be as shown in the following example:



1.2.1 Device types. The device types shall identify the circuit function as follows:

Device type	Generic number	Circuit function	Access time
01	See 6.6	16K x 4 Static RAM	25 ns (data retention)
02	See 6.6	with $\overline{\text{OE}}$ and dual $\overline{\text{CE}}$	25 ns
03	See 6.6		20 ns (data retention)
04	See 6.6		20 ns
05	See 6.6		<pre>15 ns (data retention)</pre>
06	See 6.6		15 ns

1.2.2 Case outlines. The case outlines shall be as designated in appendix C of MIL-M-38510, and as follows:

Outline letter

Case outline

L D-9 (24-lead, 1.280" x .310" x .200"), dual-in-line package X C-11 (28-terminal, .560" x .358" x .120") leadless chip carrier package

1.3 Absolute maximum ratings.

1.4 Recommended operating conditions.

 $\overline{Z}/\overline{ATT}$ voltages referenced to V_{SS} . $\overline{Z}/\overline{V_{IL}}$ negative undershoots to a minimum of -2.0 V dc are allowed with a maximum 20 ns pulse width.

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DEFENSE ELECTRONICS SUPPLY CENTER DAYTON, OHIO 45444

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2	A DDI	TCARLE	DOCUMEN	ITS

2.1 Government specification, standard, and bulletin. Unless otherwise specified, the following specification, standard, and bulletin of the issue listed in that issue of the Department of Defense Index of Specifications and Standards specified in the solicitation, form a part of this drawing to the extent specified herein.

SPECIFICATION

MILITARY

MIL-M-38510

- Microcircuits, General Specification for.

STANDARD

MILITARY

MIL-STD-883

- Test Methods and Procedures for Microelectronics.

BULLETIN

MILITARY

MTI -BUL-103

- List of Standardized Military Drawings (SMD's).

(Copies of the specification, standard, and bulletin required by manufacturers in connection with specific acquisition functions should be obtained from the contracting activity or as directed by the contracting activity.)

2.2 Order of precedence. In the event of a conflict between the text of this drawing and the references cited herein, the text of this drawing shall take precedence.

3. REQUIREMENTS

- 3.1 Item requirements. The individual item requirements shall be in accordance with 1.2.1 of MIL-STD-883, "Provisions for the use of MIL-STD-883 in conjunction with compliant non-JAN devices" and as specified herein.
- 3.2 Design, construction, and physical dimensions. The design, construction, and physical dimensions shall be as specified in MIL-M-38510 and herein.
 - 3.2.1 Terminal connections. The terminal connections shall be as specified on figure 1.
 - 3.2.2 Truth table. The truth table shall be as specified on figure 2.
 - 3.2.3 Case outlines. The case outlines shall be in accordance with 1.2.2 herein.
- 3.2.4 Die overcoat. Polyimide and silicone coatings are allowable as an overcoat on the die for alpha particle protection provided that each coated microcircuit inspection lot (reference MIL-M-38510, 3.1.3.8) shall be subjected to and pass the internal moisture content test, (test method 1018 of MIL-STD-883). The frequency of the internal water vapor testing may not be decreased unless approved by the preparing activity.
- 3.3 Electrical performance characteristics. Unless otherwise specified herein, the electrical performance characteristics are as specified in table I and shall apply over the full case operating temperature range.
- 3.4 Electrical test requirements. The electrical test requirements shall be the subgroups specified in table II. The electrical tests for each subgroup are described in table I.

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- 3.5 Marking. Marking shall be in accordance with MIL-STD-883 (see 3.1 herein). The part shall be marked with the part number listed in 1.2 herein. In addition, the manufacturer's part number may also be marked as listed in MIL-BUL-103 (see 6.6 herein).
- 3.6 Certificate of compliance. A certificate of compliance shall be required from a manufacturer in order to be listed as an approved source of supply in MIL-BUL-103 (see 6.6 herein). The certificate of compliance submitted to DESC-ECS prior to listing as an approved source of supply shall affirm that the manufacturer's product meets the requirements of MIL-STD-883 (see 3.1 herein) and the requirements herein.
- 3.7 Certificate of conformance. A certificate of conformance as required in MIL-STD-883 (see 3.1 herein) shall be provided with each lot of microcircuits delivered to this drawing.
- 3.8 Notification of change. Notification of change to DESC-ECS shall be required in accordance with MIL-STD-883 (see 3.1 herein).
- 3.9 Verification and review. DESC, DESC's agent, and the acquiring activity retain the option to review the manufacturer's facility and applicable required documentation. Offshore documentation shall be made available onshore at the option of the reviewer.
 - 4. QUALITY ASSURANCE PROVISIONS
- 4.1 Sampling and inspection. Sampling and inspection procedures shall be in accordance with section $\frac{4}{1}$ of MIL-M-38510 to the extent specified in MIL-STD-883 (see 3.1 herein).
- 4.2 <u>Screening</u>. Screening shall be in accordance with method 5004 of MIL-STD-883, and shall be conducted on all devices prior to quality conformance inspection. The following additional criteria shall apply:
 - a. Burn-in test, method 1015 of MIL-STD-883.
 - Test condition D using the circuit submitted with the certificate of compliance (see 3.6 herein).
 - (2) $T_A = +125^{\circ}C$, minimum.
 - b. Interim and final electrical test parameters shall be as specified in table II herein, except interim electrical parameter tests prior to burn-in are optional at the discretion of the manufacturer.
- 4.3 Quality conformance inspection. Quality conformance inspection shall be in accordance with method $\overline{5005}$ of MIL-STD-883 including groups A, B, C, and D inspections. The following additional criteria shall apply.
 - 4.3.1 Group A inspection.
 - a. Tests shall be as specified in table II herein.
 - b. Subgroups 5 and 6 in table I, method 5005 of MIL-STD-883 shall be omitted.
 - c. Subgroup 4 ($C_{ ext{IN}}$ and $C_{ ext{OUT}}$ measurements) shall be measured for the initial characterization and after any process or design changes which may affect capacitance. Sample size is fifteen devices with no failures, and all input and output terminals tested.
 - d. Subgroup 7 and 8 tests sufficient to verify the truth table.

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Test	 Symbol		Group A Group A subgroups		Limi	ts	Unit
	! !	V _{SS} = 0 V, 4.5 V < V _{CC} < 5.5 V unless otherwise specified		ijpes .	Min	Max	
Input leakage current	ILI	$ V_{CC} = max$, $V_{IN} = GND$ to V_{CC}	1,2,3	A17		10	μА
Output leakage current	 I I L O	$V_{CC} = max$, $V_{OUT} = GND$ to V_{CC} $\frac{ CE }{ CE } \ge V_{IH}$ $\overline{WE} \le V_{IL}$	1,2,3	A11		10	μ Α
Output low voltage	I V _{OL}		1,2,3	All	 	0.4	V
Output high voltage	I V _{OH} I		1,2,3	 All 	2.4		 V
Operating supply current	I _{CC1}		1,2,3	 01,03 		120	 m/
	 		 	02,04		130	Γ
	 	 	- 	 05,06 	 	150	T ! !
Standby power supply current	I CC2		1,2,3	01,03,05		20	l mA
(TTL)	<u> </u>		<u> </u>	02,04,06	j I	50	i I
Standby power supply current	1CC3	V _{CC} +0.2 V > CE > V _{CC} -0.2 V loutputs open	1,2,3	01,03,05		5	mA
(CMOS)	 	$ V_{CC} ^{+0.2} V \ge V_{IN} \ge V_{CC}^{-0.2} V$ $ Or ^{+0.2} V \ge V_{IN} \ge -0.2 V$ f = 0 Hz	 	02,04,06	 	20	! ! !
Data retention current	I I CC4	1 1 1 1 V _{CC} = V _{DR} 1 = 2.0 V	1,2,3	01,03,05		600	 μΑ
Input capacitance <u>1</u> /	ICIN	 V _I = 0 V f = 1 MHz, T _A = +25°C See 4.3.1c	 4 	 A11 	 - -	10 10	 pF
Output capacitance <u>1</u> /	C _{OUT}		 4 	 A11 	 	 10 	 pF

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Test	Symbol		Conditions	Group A	Device	Lim	its	Unit
	 	-55 C V _{SS} = 0 V, unless o	$4.5 \text{ V}_{\odot} < 125^{\circ}\text{C}$ $4.5 \text{ V}_{\odot} < 125^{\circ}\text{C}$ therwise specified	subgroups 	types 	 Min	 Max	
Read cycle time	tavav	2/3/4/		9,10,11	01,02	25] 	l ns
		 			03,04	20	! 	
	 	 			05,06	15		T
Address cycle	it _{AVQV}	T 		9,10,11	01,02		25	ns
t the		i !			03,04		 20	
	 	! 			 05,06 		 15 	
Chip-enable access time	tELQV	T ! !		9,10,11	01,02	I I	25	ns
doctor vine	<u> </u> 	 		i i	03,04	<u> </u> 	20	<u> </u>
	 	 		1	 05,06 	1	 15 	
Output hold from address change	t _{AVQX}			9,10,11	 A11 	0	 	ns
Output enable to output valid	t _{OLQV}	 		9,10,11	 A11 	 	15 	l ns
Chip select to output in low-Z 1/5/	t _{ELQX}	 		9,10,11	 A11 	3	 	ns
Output enable to output in low-	t _{OLQX}	 		9,10,11	A11	3	 	ns
Chip select to output in high-	i t _{EHQZ} 	 		9,10,11	A11		10	ns
Output disable to output in high-Z 1/5/	t _{OH QZ}			9,10,11	A11] 	10	l ns
See footnotes at e	end of ta	ble.						
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	TABLE I	. Electrical pe	erformance	charac	teristics - Co	ntinued.			
Test	Symbol	Co	nditions	•	Group A	Device	Lim	its	 Unit
	l	-55°C < T V _{SS} = 0 V, 4 unless oth	C <+125°C .5 V < VCC erwise spe	< 5.5 cified	subgroups V	types	Min	Max	
output in high-	t _{WLQZ}	<u>2/ 3/ 4/</u>			9,10,11	01,02	 	15	ns
Z <u>1/5</u> /	 					03,04		12	 - -
] -			<u> </u>	05,06		10	i
Data valid to end of write	l Itdywh I				9,10,11	01,02	15	! ! !	l ns
	 					03,04	12		- - -
	 	 				05,06	10	 	
Data hold time	t _{WHDX}				9,10,11	All	0	1	l ns
Output active from end of write 1/5/write	I twhqx 				9,10,11	 A]] 	 3 	 	ns
Write-cycle time <u>1</u> /	I I ^t avav I				9,10,11	01,02	25	 	ns
	 					03,04	20	 	<u> </u> -
		 -				05,06	15	<u> </u>	<u> </u>
end of write	t _{ELWH}	 			9,10,11	01,02	20		<u> </u>
<u>4</u> /	 					03,04	17		ns
	<u> </u>	! -				05,06	14	<u> </u>	<u> </u>
Address valid to end of write	tavwH	 			9,10,11	01,02	20	<u> </u>	<u> </u>
	 	; 				03,04	17	<u> </u> 	i ns
						05,06	14	<u> </u>	<u> </u>
See footnotes at	end of ta	ble.							
STAND MILITAR	ARDIZE V DRAV	_	SIZE A				5962-89	891	
DEFENSE ELECT		PPLY CENTER		'	REVISION LEVEL		SHEET	7	

	TABLE	I. Electrical performance character	istics - Co	ontinued.			
Test	Symbol	Conditions	Group A	Device	Lim	its	Unit
		$ \begin{array}{cccccccccccccccccccccccccccccccccccc$	subgroups 	i types 	Min	Max	!
Address-setup time	tavwl	2/3/4/	9,10,11	 A11 	0	 	ns
Write pulse width	twLwH	 	9,10,11	 01,02 	20		
	 	 		1 03,04 	17		 ns
] 	 	05,06	14		1
Write recovery time	 tehax 	T 	9,10,11	 01-06 	0		l ns
Chip disable to data retention time	t _{CDR}	T 	9,10,11	01,03,05	0		ns
Data retention recovery time	it _R		9,10,11	01,03,05	tavav		ns

 $[\]underline{1}$ / This parameter tested intially and after any design or process change which could affect this

 $\underline{4}$ / Both chip selects must be active low for the device to be selected.

5/ Transition is measured ±500 mV from steady state.

4.3.2 Groups C and D inspections.

- a. End-point electrical parameters shall be as specified in table II herein.
- b. Steady-state life test conditions, method 1005 of MIL-STD-883:
 - (1) Test condition D using the circuit submitted with the certificate of compliance (see 3.6 herein).
 - (2) $T_A = +125^{\circ}C$, minimum.
 - (3) Test duration: 1,000 hours, except as permitted by method 1005 of MIL-STD-883.

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parameter, and is therefore guaranteed to the limits specified in table I.

2/ For timing waveforms, see figure 3.

3/ AC parameters are tested using input rise and fall times of 5 ns and input pulse levels of GND to 3.0 V. Both input and output timing reference levels are 1.5 V, and the output load is shown on figure 4.

10	01	06
Device types	01 -	06 T
Case outlines	i L	i x i
 Terminal number	Terminal symbol	
2 3 4 5 6 7	A1 A2 A3 A4 A5 A6	INC INC IAO IA1 IA2 IA3 IA4
9	1A ₈	A6
11	<u>oe</u>	 A ₈
12	GND	CE ₁
13 14	WE 1/0 ₁	OE I
15	1/02	CE ₂
16 17	I/03 I/04	WE 1/0 ₁
19 20 21 22	A ₁₀ A ₁₁ A ₁₂ A ₁₃ VCC	I/O2 I/O3 I/O4 A9 A10 A11 A12 A13 NC VCC

NC = no connection

FIGURE 1. Terminal connections.

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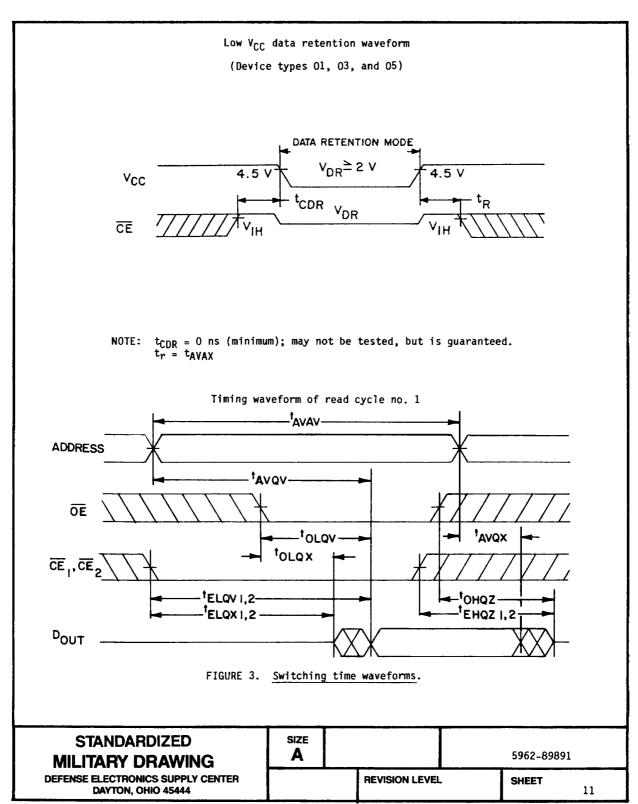
Mode	CE ₁	CE ₂	I WE	ŌĒ	1/0	 Power
Standby	H 	 X 	i X	X	 High-Z 	Standby
 Standby	X	Т Н 	I X	X 	 High-Z 	 Standby
Read	L	 L 	 H	L	DOUT	Active
Write	 L 	l L	l L	 X 	DIN	Active
 Read 	L	L L	H	 H 	High-Z	Active

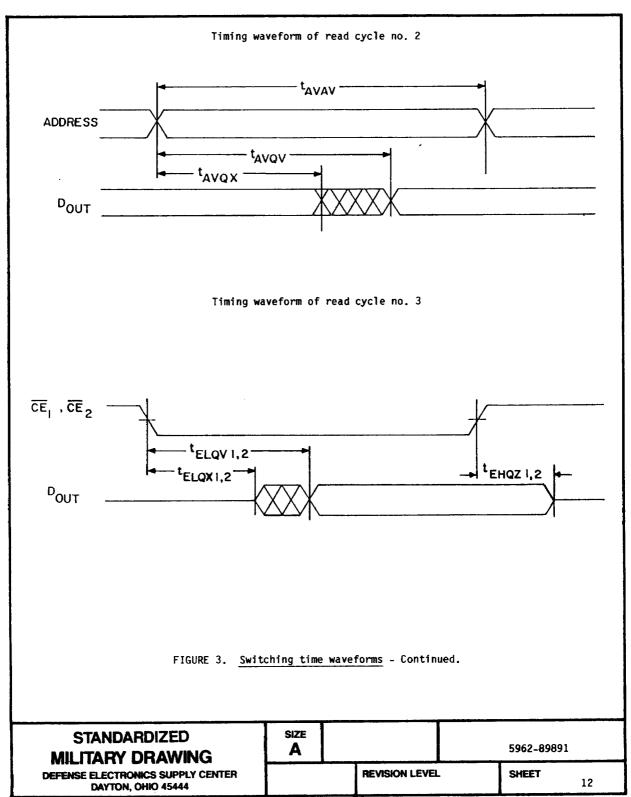
FIGURE 2. Truth table.

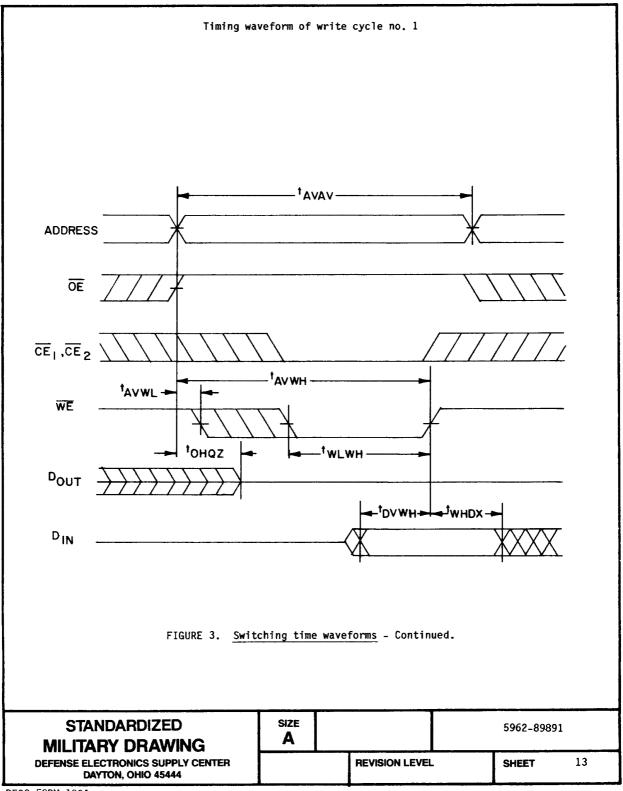
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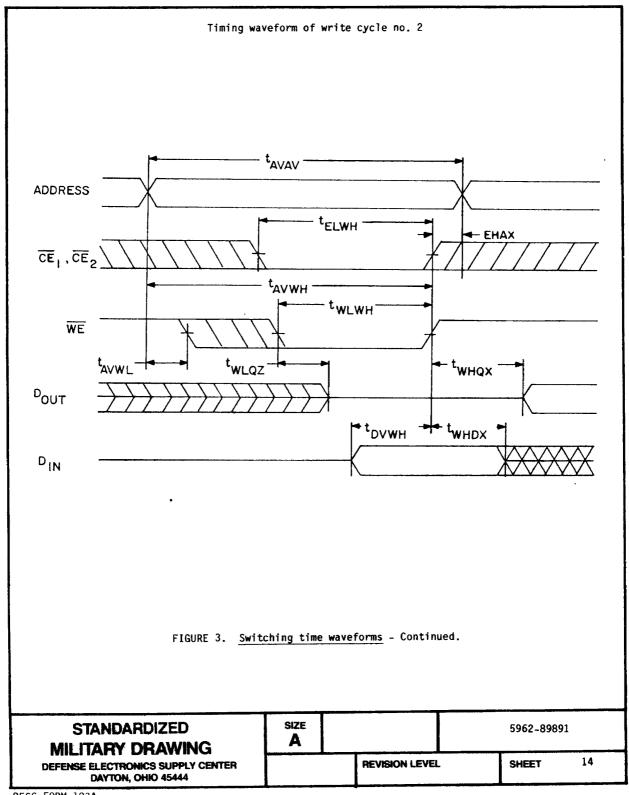
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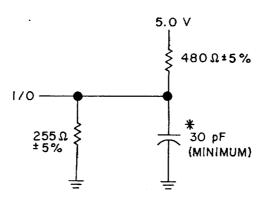
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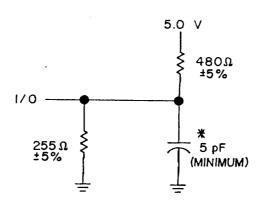








Circuit A or equivalent



Circuit B or equivalent

for (t_{ELQX} , t_{OLQX} , t_{EHQZ} , t_{OHQZ} , t_{WLQZ} , t_{WHQX})

*Including scope and jig

FIGURE 4. Output load circuits.

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TABLE II. Electrical test requirements.

MIL-STD-883 test requirements MIL-STD-883 test requirements 	Subgroups (per method 5005, table I)
 Interim electrical parameters (method 5004)	
	1*,2,3,7*,8A, 8B,9,10,11
Group A test requirements (method 5005)	1 1,2,3,4**,7***, 1 (8A,8B)***,9,10,11
Groups C and D end-point electrical parameters (method 5005)	2,3,7,8A,8B

- * PDA applies to subgroup 1 and 7
- ** See 4.3.1c.
- *** See 4.3.1d.

5. PACKAGING

5.1 Packaging requirements. The requirements for packaging shall be in accordance with MIL-M-38510.

6. NOTES

- 6.1 Intended use. Microcircuits conforming to this drawing are intended for use when military specifications do not exist and qualified military devices that will perform the required function are not available for OEM application. When a military specification exists and the product covered by this drawing has been qualified for listing on QPL-38510, the device specified herein will be inactivated and will not be used for new design. The QPL-38510 product shall be the preferred item for all applications.
- 6.2 Replaceability. Microcircuits covered by this drawing will replace the same generic device covered by a contractor-prepared specification or drawing.
- 6.3 Configuration control of SMD's. All proposed changes to existing SMD's will be coordinated with the users of record for the individual documents. This coordination will be accomplished in accordance with MIL-STD-481 using DD Form 1693, Engineering Change Proposal (Short Form).
- 6.4 Record of users. Military and industrial users shall inform Defense Electronics Supply Center when a system application requires configuration control and the applicable SMD. DESC will maintain a record of users and this list will be used for coordination and distribution of changes to the drawings. Users of drawings covering microelectronics devices (FSC 5962) should contact DESC-ECS, telephone (513) 296-6022.
- 6.5 Comments. Comments on this drawing should be directed to DESC-ECS, Dayton, Ohio 45444, or telephone (513) 296-5375.

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Approved sources of supply. Approved sources of supply are listed in MIL-BUL-103. Additional sources will be added to MIL-BUL-103 as they become available. The vendors listed in MIL-BUL-103 have agreed to this drawing and a certificate of compliance (see 3.6 herein) have submitted to and accepted by DESC-ECS. The approved sources of supply listed below are for information purposes only and are current only to the date of the last action of this document.

 Military drawing part number 	Vendor CAGE number	Vendor similar part number 1/
 5962-8989101LX / 	 61772 75569	7198L25CB
 5962-8989101XX	61772	7198L25L28B
5962-8989102LX	61772 75569	 7198S25CB
 5962-8989102XX	61772	 7198S25L28B
5962-8989103LX -	61772	
5962-8989103XX	61772	
 5962-8989104LX /	 61772 75569	
 5962-8989104XX /	61772	
 5962-8989105LX/	61772	
 5962-8989105XX /	61772	7198L15L28B
5962-8989106LX /	61772 75569	7198S15CB
 5962-8989106XX /	61772	7198S15L28B

1/ Caution. Do not use this number for item acquisition. Items acquired to this number may not satisfy the performance requirements of this drawing.

number and address 61772 Integrated Device Technology, Incorporated 1566 Moffet Boulevard Salinas, CA 95054 Point of contact: 3236 Scott Boulevard Santa Clara, CA 95054 75569 ${\bf Performance\ Semiconductor\ Corporation}$ 610 East Weddell Drive Sunnyvale, CA 94089

STANDARDIZED MILITARY DRAWING

SIZE Α

Vendor CAGE

5962-89891

DEFENSE ELECTRONICS SUPPLY CENTER DAYTON, OHIO 45444

REVISION LEVEL

Vendor name

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